

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	"6156581".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 14:20
L2	8	"6156581".pn. "20030015708" "5175597".pn. "5006488".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 14:20
L3	10	"6156581".pn. "20030015708" "5175597".pn. "5006488".pn. "5929467".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 14:26
L4	1	(titanium or ti) and (nickel or ni) and 3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 14:33
L5	0	pitch and 3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 14:30
L6	0	aspect adj ratio and 3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 14:28
L7	0	"1:3" and 3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 14:29
L8	0	"1:1" and 3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 14:29

EAST Search History

L9	10	pitch and permeable adj base adj transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 14:41
L10	31	(titanium or ti) and (nickel or ni) and permeable adj base\$4 adj transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 14:33
L11	15	((("6156581") or ("5929467") or ("4224361") or ("5215619") or ("5175597") or ("4510016") or ("5006488")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/16 14:42
L12	0	anneal and 11	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 14:42
L13	0	anneal\$4 and 11	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 14:45
L14	13403	anneal\$4 with contact	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 14:45
L15	2	anneal\$4 with contact with (reverse adj leak adj current)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 15:36
L16	2	"6690042".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 15:49
L17	0	"6690042".pn. and (sin or silicon adj nitride)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 15:36

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L18	0	"6690042".pn. and photoresist	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 15:49
L19	0	"6690042".pn. and resist	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 15:49
L20	0	"6690042".pn. and mask	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 16:56
L21	73	438/173.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 16:56
L22	144	438/343.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 16:57
L23	117	438/347.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 16:57
L24	139	438/520.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 16:57
L25	95	438/576.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 16:57
L26	66	438/577.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 16:57

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L27	316	438/for.173.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 16:57
L28	190	257/e29.185.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 16:57
L29	11	257/e29.178.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 16:57
L30	44	257/e21.451.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 16:58
L31	617	438/951.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 16:58
S1	40970	gan or gallium adj nitride	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 11:30
S2	1500	hvpe or hydride adj vapor adj phase adj epitaxy	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 08:38
S3	45306	sapphire	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 05:54
S4	113330	helium	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 05:59

EAST Search History

S5	49	S1 and S2 and S3 and S4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 05:59
S6	3	((("3966501") or ("6410396") or ("6545340"))).PN.	USPAT	OR	OFF	2006/06/14 06:48
S7	2	("20020177685").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/14 06:03
S8	14735	molecular adj beam adj epitaxy	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 06:03
S9	35	S5 and S8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 06:12
S11	4	((("3966501") or ("6410396") or ("6545340") or ("6533874"))).PN.	USPAT	OR	OFF	2006/06/14 06:50
S12	32856	lift adj off or lift-off	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 15:34
S13	152	438/92.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 06:52
S14	362	438/312.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 06:52
S15	117	438/347.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 06:55

EAST Search History

S16	1174	438/514.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 06:55
S17	125	438/520.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 06:55
S18	452	438/528.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 06:55
S19	200	permeable adj base adj transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 08:37
S20	7	S1 and S3 and S19	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/14 06:56
S21	35990	lift adj off or liftoff	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 08:37
S22	845798	transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 08:43
S23	6243	S21 and S22	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 08:44
S24	42342	gan or gallium adj nitride	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 08:44

EAST Search History

S25	1595	hvpe or hydride adj vapor adj phase adj epitaxy	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 08:44
S26	1379	S24 and S25	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 08:54
S27	102	S23 and S26	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 08:44
S28	299358	emitter	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 08:54
S29	1832566	collect\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 08:55
S30	172218	S28 and S29	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 08:55
S31	35	S26 and S30	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 08:55
S32	5000895	base	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 08:55
S33	150530	S30 and S32	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 08:56

EAST Search History

S34	27	S31 and S33	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 08:56
S35	4	((("3966501") or ("6410396") or ("6545340") or ("6533874"))).PN.	USPAT	OR	OFF	2006/08/31 15:34
S36	33574	lift adj off or lift-off	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 15:34
S37	1	S35 and S36	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 15:34
S38	13	("4144116" "4622093" "4727047" "4888303" "4931132" "5210051" "5393993" "5679152" "5679965" "5777350" "5810925" "5874747" "5923946").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/08/31 15:48
S39	2	S36 and S38	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/31 15:48
S40	3	etch\$3 near5 base adj layer and (decreas\$3 or rampdown or ramp adj down or ramp-down) near7 bias adj voltage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 10:08
S41	3	etch\$3 near7 base adj layer and (decreas\$3 or rampdown or ramp adj down or ramp-down) near7 bias adj voltage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 10:08
S42	1697	(decreas\$3 or rampdown or ramp adj down or ramp-down) near7 bias adj voltage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 10:08

EAST Search History

S44	307	etch\$3 and S42	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 12:00
S45	20	"n+ GaN layer" and "n- GaN layer"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 10:37
S46	66	(he or helium) adj (implantation or implant\$4) near7 (layer or liner or film)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 10:55
S47	0	(he or helium) adj (implantation or implant\$4) near7 "n+" adj (layer or liner or film)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 10:38
S48	78	(he or helium) adj (implantation or implant\$4) near12 (layer or liner or film)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 10:57
S49	12	S48 not S46	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 11:18
S50	919	(he or helium) near7 (implantation or implant\$4) same (layer or liner or film)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 10:58
S51	107	(he or helium) near7 (implantation or implant\$4) same insulat\$4 adj (layer or liner or film)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 10:58
S52	29	("5929467").URPN.	USPAT	OR	ON	2006/09/19 11:11

EAST Search History

S53	3	"2000068605"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 11:19
S54	2	"6156581".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 12:11
S55	88	(ebeam or electronic adj beam) adj lithography	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 12:22
S57	130	438/520.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 12:26
S58	463	438/528.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 12:26
S59	824	438/597.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 12:39
S60	94	etch\$3 adj grooved	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 12:41
S61	36161	liftoff or lift adj off or lift-off	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 12:50
S62	238005	metal adj (layer or liner or film)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 12:51

EAST Search History

S63	1003	S61 near5 S62	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 12:55
S67	216959	ebeam or e-beam or e adj beam or electron adj beam	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 12:55
S68	277	S63 and S67	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 14:16
S69	17358	collect\$4 adj region	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 14:31
S70	849218	transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 17:16
S71	12474	S69 and S70	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 14:18
S72	300143	emitter	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 14:18
S73	11147	S71 and S72	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 14:18
S74	61086	base adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 14:18

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S75	1695	S73 and S74	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 14:19
S76	42655	gan or gallium adj nitride	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 14:19
S77	66	S76 and S75	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 14:20
S78	41897	contact adj pad	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 14:20
S79	53	S75 and S78	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 15:36
S80	2	collect\$4 adj region and finger adj pitch	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 14:38
S81	455	titanium/nickel or ti/ni	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 14:43
S82	1	S75 and S81	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 14:39
S83	462028	(titanium or ti) and (nickel or ni)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 14:43

EAST Search History

S84	147	S75 and S83	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 16:41
S85	12	("4903104").URPN.	USPAT	OR	ON	2006/09/19 14:46
S86	2	("4712121" "4739379").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/09/19 14:48
S87	1	collector near2 pad near10 (silicon adj nitride or sin or "si.sub.3.n. sub.4")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 15:37
S88	1	collector near4 pad near10 (silicon adj nitride or sin or "si.sub.3.n. sub.4")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 15:37
S89	20	collector near4 pad same (silicon adj nitride or sin or "si.sub.3.n. sub.4")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 15:42
S90	1912	438/149.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 15:41
S91	1247	collector near4 pad	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 15:43
S92	687	collector near2 pad	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 15:43
S93	1	S90 and S92	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 15:43

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S95	1	S90 and S91	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 15:44
S96	40	collect\$2 adj contact adj pad	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 15:58
S97	458	438/for.455.CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 15:59
S98	1	RF adj test adj pad	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 16:41
S99	4501	test adj pad	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 16:41
S10 0	1	S90 and S99	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 17:14
S10 1	2245	438/14.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 17:15
S10 3	2203	contact adj pad near4 test\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 17:16
S10 4	54	S101 and S103	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 17:16

EAST Search History

S10 5	13	(gallium nitride or gan) and (ion adj implant\$4 or ion adj implantation or dop\$4) and collector adj finger	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 08:10
S10 6	4	(gallium nitride or gan) and (ion adj implant\$4 or ion adj implantation or dop\$4) and collector adj finger and (collect\$4 near2 pad)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 07:42
S10 7	5626	emitter and base and collector and base adj contact	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 07:58
S10 8	86	438/91.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 07:58
S10 9	287	438/167.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 07:58
S11 0	40	438/169.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 07:58
S11 1	42	438/534.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 07:59
S11 2	491	438/570.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 07:59
S11 3	316	438/for.173.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 07:59

EAST Search History

S11 4	9	438/for.197.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 07:59
S11 5	70	438/for.198.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 07:59
S11 6	283	438/for.181.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 07:59
S11 7	184	438/for.335.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 08:00
S11 8	176	438/for.336.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 08:00
S11 9	149	438/for.337.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 08:00
S12 0	42	438/for.338.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 08:00
S12 1	47	438/for.339.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 08:00
S12 2	1639	438/571.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 08:00

EAST Search History

S12 3	157	438/572.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 08:00
S12 4	93	438/573.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 08:00
S12 5	66	438/577.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 08:00
S12 6	37	S107 and S122	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 08:06
S12 7	6189	(helium or he) with (implant\$4 or implantation or dop\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 09:53
S12 8	449372	(gallium nitride or gan)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 08:10
S12 9	155175	(ion) with (implant\$4 or implantation or dop\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 08:10
S13 0	10	S122 and S127	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 08:12
S13 1	765	S122 and (S128 or S129)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 08:37

EAST Search History

S13 2	.1	rf adj test adj pad	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 08:15
S13 3	4712	test adj pad	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 08:40
S13 4	0	(S122 or S123 or S124) and S133	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 08:15
S13 5	105	257/73.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 08:38
S13 6	0	(S108 or S109 or S110 or S111 or S112) and S133	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 08:40
S13 7	0	(S113 or S114 or S115 or S116 or S117 or S118) and S133	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 08:40
S13 8	1	test adj pad and 10/532456.app.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 08:39
S13 9	5300	test\$4 adj pad	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 08:40
S14 0	0	(S108 or S109 or S110 or S111 or S112) and S139	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 08:40

EAST Search History

S14 1	0	(S113 or S114 or S115 or S116 or S117 or S118) and S139	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 08:42
S14 2	1326	collector with (sin or silicon adj nitride)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 08:43
S14 3	285	S107 and S142	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 08:55
S14 4	254	test\$4 with schottky	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 09:20
S14 5	2	"20030015708"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 09:21
S14 6	0	(09/911155).APP.	USPAT; USOCR	OR	ON	2007/02/27 09:23
S14 7	9	(S119 or S120 or S121 or S122 or S123 or S124 or S125) and S127	USPAT; USOCR	OR	ON	2007/02/27 09:24
S14 8	1875	S127 and S128	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 09:25
S14 9	553	S148 and diode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 09:28
S15 0	2	"20020117658"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/27 09:28
S15 1	1	(10/005170).APP.	USPAT; USOCR	OR	ON	2007/02/27 09:29

EAST Search History

S15 2	1	"3966501".pn.	USPAT; USOCR	OR	ON	2007/02/27 09:31
S15 3	1	"6410396".pn.	USPAT; USOCR	OR	ON	2007/02/27 09:35
S15 4	7	emitter adj (area or region) with S127	USPAT; USOCR	OR	ON	2007/02/27 09:35
S15 5	1804	hvpe or hydride adj vapor adj phase adj epitaxy	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/14 10:30
S15 6	491325	ion adj (implantation or implant\$4) or dop\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/14 10:31
S15 7	1828661	helium or he	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/14 10:31
S15 8	220599	electron adj beam or e-beam	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/14 10:31
S15 9	1370	S155 and S156	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/14 10:31
S16 0	25990	S157 and S158	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/14 10:31
S16 1	51	S159 and S160	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/14 10:32
S16 2	4738	test adj pad	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/14 10:33

EAST Search History

S16 3	44179	contact adj pad	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/14 10:39
S16 4	1	S161 and S162	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/14 10:33
S16 5	4	S161 and S163	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/14 10:33
S16 6	94	collector adj finger	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/14 10:39
S16 7	1	S155 and S156 and S157 and S163 and S166	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/14 10:40
S16 8	81812	ohmic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/14 10:40
S16 9	92	(contact adj pad) near5 (silicon adj nitride or sin)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/14 12:08
S17 0	2	"6156581".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/14 12:12
S17 1	308331	emitter	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/14 12:12

EAST Search History

S17 2	5185240	base	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/14 12:12
S17 3	44179	contact adj pad	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/14 12:12
S17 4	421720	collector	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/14 12:12
S17 5	45829	gan or gallium adj nitride	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/14 12:12
S17 6	34709	schottky	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/14 12:13
S17 7	925	S171 and S172 and S173 and S174	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/14 13:48
S17 8	1763	S175 and S176	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/14 12:14
S17 9	5	S177 and S178	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/14 12:16
S18 0	44	S177 and S175	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/14 12:21

EAST Search History

S18 1	39	collector adj contact adj pad	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/14 14:05
S18 2	275	438/93.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/14 13:47
S18 3	383	438/312.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/14 13:06
S18 4	1803134	semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/14 13:48
S18 5	730	S177 and S184	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/14 13:48
S18 6	82	("4914058").URPN.	USPAT	OR	ON	2007/03/14 13:57
S18 7	816	isolation adj pad	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/14 14:05
S18 8	0	S183 and S187	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/14 14:05
S18 9	0	S182 and S187	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/14 14:05

EAST Search History

S19 0	197	S184 and S187	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/14 14:05
S19 1	73	438/173.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/15 17:35
S19 2	144	438/343.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/15 17:34
S19 3	1883	permeable adj base	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/15 17:35
S19 4	206	permeable adj base adj transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 11:32
S19 5	454421	silicon adj nitride or sin	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/15 17:36
S19 6	37	S194 and S195	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/15 17:36
S19 7	30	("4510016").URPN.	USPAT	OR	ON	2007/03/15 17:47
S19 8	1	1989-214972.NRAN.	DERWENT	OR	ON	2007/03/15 17:55
S19 9	1	1996-059270.NRAN.	DERWENT	OR	ON	2007/03/15 18:03
S20 0	1	1996-059270.NRAN.	DERWENT	OR	ON	2007/03/15 18:03

EAST Search History

S20 1	206	permeable adj base adj transistor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/15 18:06
S20 2	10	("4144116" "4622093" "4727047" "4931132" "5210051" "5679152" "5777350" "5810925" "5874747" "5923946").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/03/15 18:09
S20 3	29	permeable adj base adj transistor and pad	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 12:04
S20 4	4	("4104673" "4639753" "5012315" "5289027").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/03/16 11:38
S20 6	73	438/173.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 12:04
S20 7	454421	silicon adj nitride or sin	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 12:04
S20 8	29	S206 and S207	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 12:04
S20 9	37	permeable adj base adj transistor and S207	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/16 14:20
S21 0	7	("3893155" "4007297" "4098921" "4212022" "4466008" "4543320" "4547789").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/03/16 12:07
S21 1	9	("4620207").URPN.	USPAT	OR	ON	2007/03/16 12:08
S21 2	20	("4510016").PN. OR ("5175597"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/03/16 12:15